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High-speed Buffer Amplifier for CCD Image Sensor

CXA3691AEN

Description

The CXA3691AEN is a high-speed buffer amplifier IC. (Applications: CCD image sensor output buffers, Digital still cameras, Camcorders, Other general buffers)

Features

- ♦ Power consumption: 24mW (typ.)

 (IDRV = 50μA (220kΩ when Vcc = 15V), ISF pin connected to GND, during no signal)
- ◆ Push-pull output
- ullet High-speed response: 500V/μs (IDRV = 50μA (220k Ω when Vcc = 15V), CL = 20pF)
- ◆ Internal sink current mode for CCD with open source output (Settable by external resistance RISF)
- ◆ Enables to set the responsibility by changing the drive current by an external resistor

Structure

Bipolar silicon monolithic IC

Absolute Maximum Ratings

(Ta = 25°C)

Supply voltage
 Vcc
 16
 V

• Supply voltage IN GND – 0.3 to Vcc + 0.3 V

Allowable power dissipation PD 0.28 W
 (when mounted on a two-layer board; 50mm × 50mm, t = 1.6mm)

Recommended Operating Conditions

Supply voltage
 Vcc
 Operating temperature
 Ta
 9.0 to 15.5
 V
 Operating temperature

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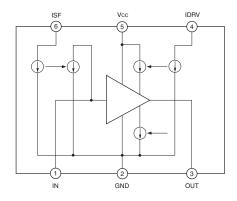


- 1 - E07712A82



Block Diagram and Pin Configuration

(Top View)



Pin Description and I/O Pin Equivalent Circuit

Pin No.	Symbol	I/O	Standard voltage level	Equivalent circuit	Description	
2	GND	_	0V	_	GND.	
5	Vcc	_	15V	_	Supply voltage input.	
1	IN	1	CCD output voltage	Vcc \$2k 10 x 10 x 10 RV 1	Input.	
6	ISF	-	1	Vcc 6 Wy 30k GND	External resistor connection for setting the sink current for CCD with open source output. Connect an external resistor between this pin and Vcc (Pin 5). Connect this pin to GND (Pin 2) when not using this function. * The minimum value of the external resistance should be $100k\Omega$ (when Vcc = 15V).	
3	OUT	0	≈IN	Vcc ₹50 3 3 GND	Output.	
4	IDRV	-		Vcc 4 Www 30k S20k GND	External resistor connection for setting the drive current. Connect an external resistor between this pin and Vcc (Pin5). * The minimum value of the external resistance should be $100k\Omega$ (when Vcc = 15V).	

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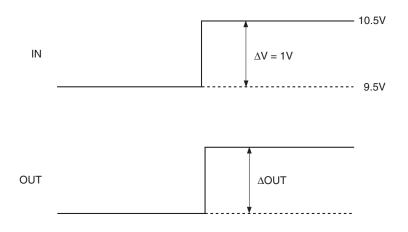
Electrical Characteristics

(Ta = 25°C, Vcc = 15V, R_{IDRV} = 220k Ω , ISF pin: connected to GND)

DC Characteristics

Item	Symbol	Measurement conditions	Min.	Тур.	Max.	Unit
Supply current	Icc	IN = 10V, Ridry = $220k\Omega$	1.4	1.6	1.8	mA
Voltage gain VGAIN		*1 IN: $10Vdc \Delta V = 1V$ GAIN = $\Delta OUT/\Delta V$	_	0.999	_	V/V
I/O offset voltage	Voffset	IN = 10V Voffset = OUT-IN	-100	_	100	mV
I/O voltage range	VRANGE	$\begin{aligned} \text{Ridrv} &= 100 \text{k}\Omega \\ \text{Ridrv} &= 150 \text{k}\Omega \\ \text{Ridrv} &= 220 \text{k}\Omega \\ \text{Ridrv} &= 330 \text{k}\Omega \end{aligned}$	3.3 2.9 2.5 2.1		Vcc - 2.0 Vcc - 1.85 Vcc - 1.8 Vcc - 1.7	V
Input bias current	IBIAS	IN = 10V, ISF = 0V	–15	- 5	6	μА
Sync current	Isink	IN = 10V, RISF = 220kΩ	2.6	2.9	3.2	mA

^{*1} Voltage gain





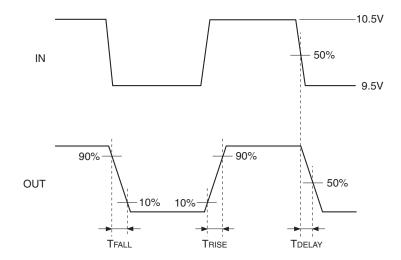


查询"CXA3691AEN"供应商 AC Characteristics

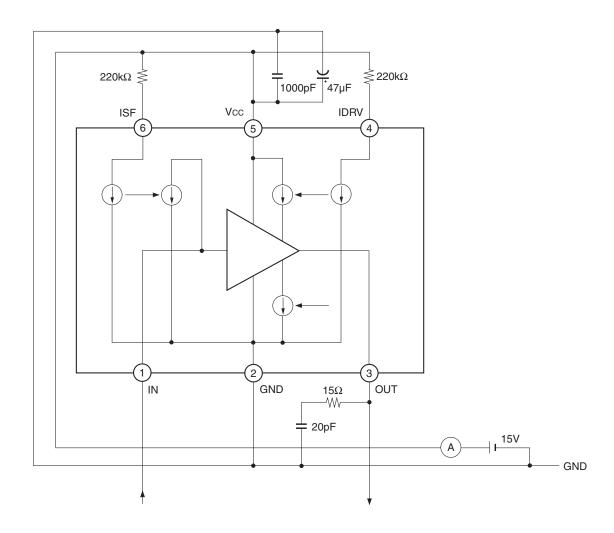
(Ta = 25°C, Vcc = 15V, IDRV = $50\mu A$ (220k Ω when Vcc = 15V), ISF pin: connected to GND, RL = 15Ω , CL = 20pF)

Item	Symbol	Measurement conditions	Min.	Тур.	Max.	Unit
Bandwidth GBW		IN = 50mVp-p	_	220	_	MHz
Rise time	Trise	*1 IN = 9.5 to 10.5V 10 to 90%	_	2.5	3.5	ns
Fall time	TFALL	*1 IN = 10.5 to 9.5V 10 to 90%	1	3.0	4.0	ns
I/O delay time	TDELAY	*1 IN = 9.5 to 10.5V @50%	0.9	1.0	2.0	ns

 $^{^{*1}}$ Rise time, fall time and I/O delay time



Evaluation Circuit



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Description of Operation

Current Settings

1. Output Drive Current

The small signal output impedance of the OUT pin (Pin 3) can be set by connecting the IDRV pin (Pin 4) to Vcc through a resistor. The inflow current to the IDRV pin is multiplied by 10 times inside the IC, and flows as the output stage idling current.

The IDRV pin has an internal $50k\Omega$ resistor, so the inflow current to the IDRV pin can be calculated as follows.

IIDRV =
$$(Vcc - VbE \times 2)/(Ridrv + 50kΩ)$$

= $(15 - 1.46)/270kΩ$
= $50.1μA$

Here, Vcc = 15V, VBE = 0.73V (typ.), and RIDRV = $220k\Omega$.

The small signal output impedance at this time can be calculated as follows.

ROUT =
$$(26\text{mV}/(10 \times \text{lidRV}))/2$$

= $(26\text{mV}/501\mu\text{A})/2$
= 26Ω

2. Sink Current for CCD with open source output

The sink current of the IN pin (Pin 6) can be set by connecting the ISF pin (Pin 1) to Vcc through a resistor. This sink current can be used as the CCD output stage source follower drive current. The inflow current to the ISF pin is multiplied by 58 times inside the IC, and flows as the sink current.

The ISF pin has an internal $50k\Omega$ resistor, so the inflow current to the ISF pin can be calculated as follows.

IISF = (VCC – VBE
$$\times$$
 2)/(RISF + 50kΩ)
= (15 – 1.46)/270kΩ
= 50.1μA

Here, Vcc = 15V, VBE = 0.73V (typ.), and RISF = 220k Ω . The sink current at this time can be calculated as follows.

$$\begin{aligned} \text{Isink} &= 58 \times \text{IISF} \\ &= 2.9 \text{mA} \end{aligned}$$

Note) This IC operation depends on IDRV and ISF.

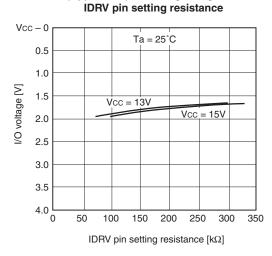
This specification is described based on IDRV of $220k\Omega$ when Vcc = 15V. However , set it to $180k\Omega$ to occur the same current when using under the condition that Vcc = 13V. [IDRV and ISF vs external resistor]

Current (μA)	90	68	50	35	26	Unit
When Vcc = 15V	100	150	220	330	470	kΩ
When Vcc = 13V	78	120	180	270	390	kΩ

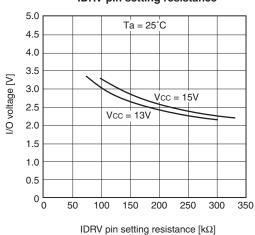


Example of Representative Characteristics

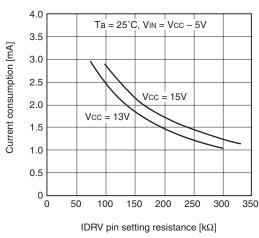
(Upper side) I/O voltage range vs.



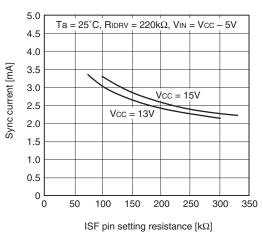
(Lower side) I/O voltage range vs. IDRV pin setting resistance



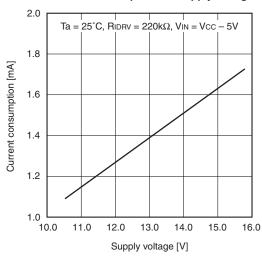
Current consumption vs. IDRV pin setting resistance



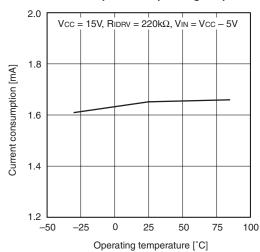
Sink current vs. ISF pin setting resistance



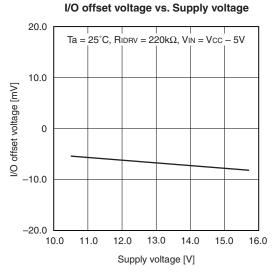
Current consumption vs. Supply voltage

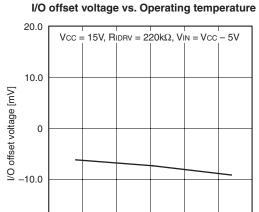


Current consumption vs. Operating temperature









-20.0

-50

-25

0

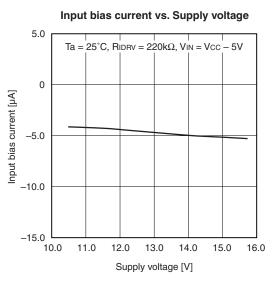
25

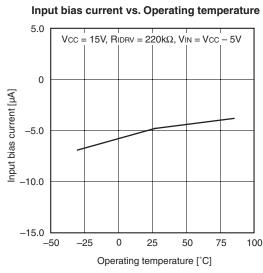
Operating temperature [°C]

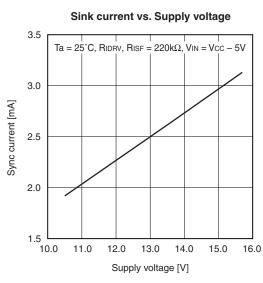
50

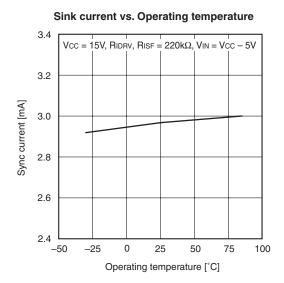
75

100

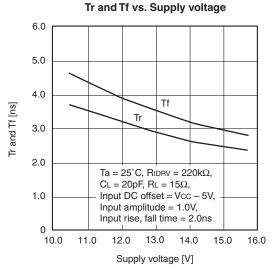


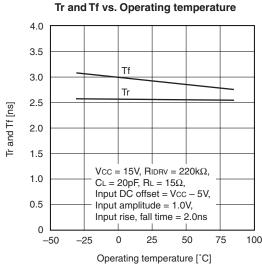


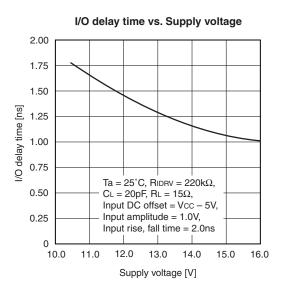


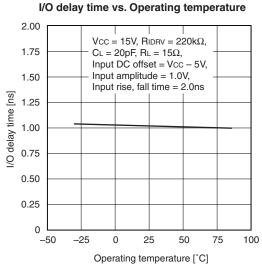


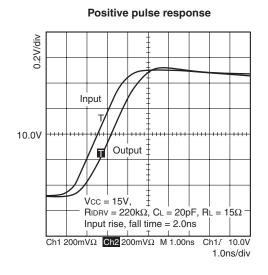


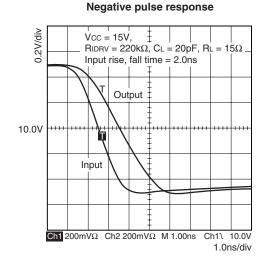




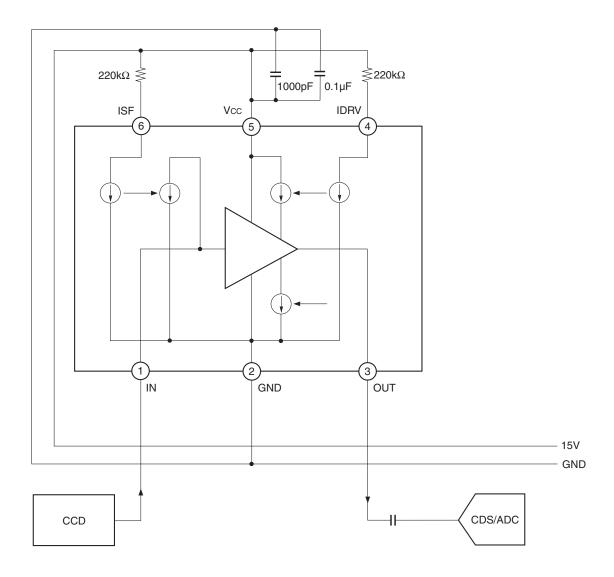






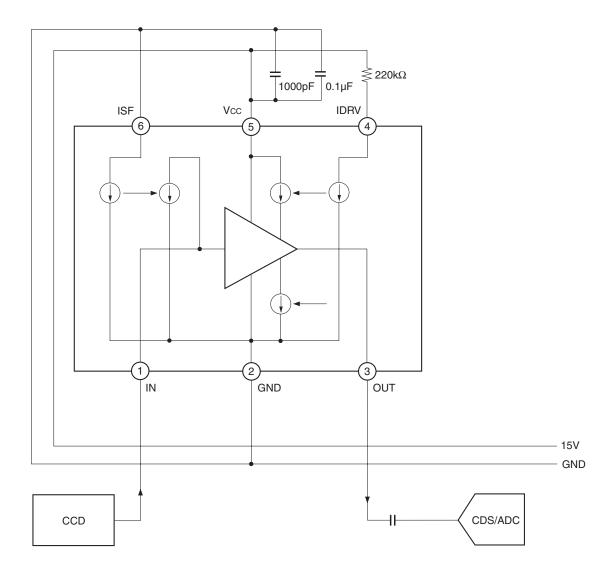


Application Circuit 1 (when using CCD with open source output)



Application circuits shown are typical examples illustrating the operation of the devices. Sony cannot assume responsibility for any problems arising out of the use of these circuits or for any infringement of third party patent and other right due to same.

Application Circuit 2 (when using CCD with internal current source)



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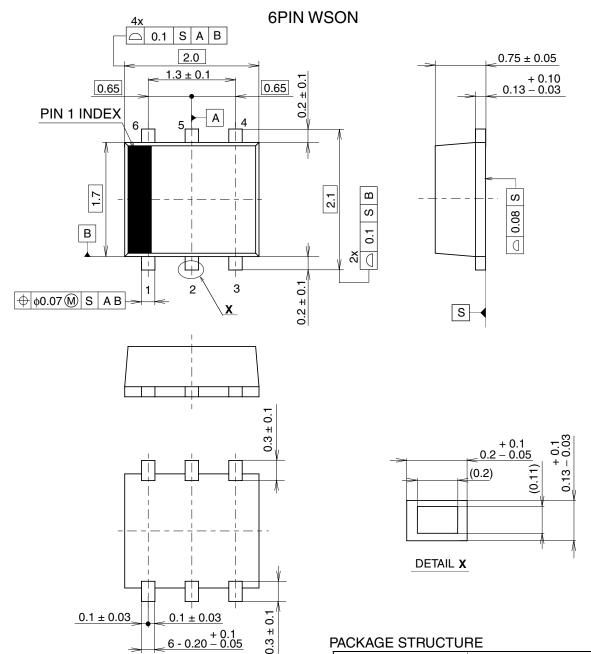
Notes on Operation

- ◆ Provide the widest GND pattern possible on the board.
- Use a 1000pF (recommended) and a 0.1μF (recommended) ceramic capacitors in parallel for the bypass capacitor connected between the power supply and GND, and connect them as close to the IC pins as possible.
- ◆ Load capacitance causes the input/output wiring response to worsen and results in noise. Use the shortest wiring layout possible, and shield it with GND.
- ◆ When the output pin (Pin 3) is shorted to either the power supply or GND, an overcurrent may flow to the output stage elements and damage them.
 When the input pin (Pin 1) is shorted to GND, an overcurrent may flow to the internal parasitic elements and damage them.



Package Outline

(Unit: mm)



SONY CODE	WSON-6P-051
EIAJ CODE	
JEDEC CODE	

+ 0.1 6 - 0.20 - 0.05



٠.	TAORAGE STROOTORE						
	PACKAGE MATERIAL	EPOXY RESIN					
	TERMINAL TREATMENT	Sn-Bi					
	TERMINAL MATERIAL	COPPER					
	PACKAGE MASS	0.008g					

LEAD PLATING SPECIFICATIONS

ITEM	SPEC.
LEAD MATERIAL	COPPER ALLOY
SOLDER COMPOSITION	Sn-Bi Bi:1-4wt%
PLATING THICKNESS	5-18µm